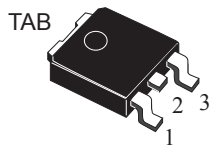
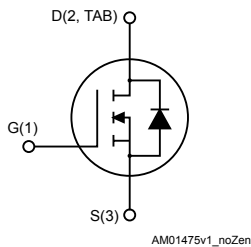


## N-channel 60 V, 0.014 $\Omega$ typ., 60 A STripFET II Power MOSFET in a DPAK package


**DPAK**


### Features

Order code	$V_{DS}$	$R_{DS(on)}$ max.	$I_D$
STD60NF06T4	60 V	0.016 $\Omega$	60 A

- Exceptional dv/dt capability
- 100% avalanche tested
- Low gate charge

### Applications

- Switching applications

### Description

This Power MOSFET series has been developed using STMicroelectronics' unique STripFET™ process, which is specifically designed to minimize input capacitance and gate charge. This renders the device suitable for use as primary switch in advanced high-efficiency isolated DC-DC converters for telecom and computer applications, and applications with low gate charge driving requirements.

#### Product status link

[STD60NF06T4](#)

#### Product summary

<b>Order code</b>	STD60NF06T4
<b>Marking</b>	D60NF06
<b>Package</b>	DPAK
<b>Packing</b>	Tape and reel

# 1 Electrical ratings

**Table 1. Absolute maximum ratings**

Symbol	Parameter	Value	Unit
$V_{DS}$	Drain-source voltage	60	V
$V_{DGR}$	Gate-source voltage ( $R_{GS} = 20\text{ k}\Omega$ )	60	V
$V_{GS}$	Gate-source voltage	$\pm 20$	V
$I_D$	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	60	A
	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	42	A
$I_{DM}^{(1)}$	Drain current (pulsed)	240	A
$P_{TOT}$	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	110	W
$I_{AR}$	Avalanche current, repetitive or not repetitive (pulse width limited by $T_{jmax}$ )	30	A
$E_{AS}^{(2)}$	Single pulse avalanche energy	350	mJ
$dv/dt^{(3)}$	Peak diode recovery voltage slope	4	V/ns
$T_{stg}$	Storage temperature range	-55 to 175	$^\circ\text{C}$
$T_j$	Operating junction temperature range		

1. Pulse width limited by safe operating area.
2. Starting  $T_J = 25\text{ }^\circ\text{C}$ ,  $I_D = I_{AR}$ ,  $V_{DD} = 30\text{ V}$
3.  $I_{SD} \leq 60\text{ A}$ ,  $di/dt \leq 200\text{ A}/\mu\text{s}$ ,  $V_{DD} \leq 24\text{ V}$ ,  $T_J \leq T_{JMAX}$

**Table 2. Thermal data**

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case	1.36	$^\circ\text{C}/\text{W}$
$R_{thj-pcb}^{(1)}$	Thermal resistance junction-pcb	50	$^\circ\text{C}/\text{W}$

1. When mounted on 1 inch<sup>2</sup> FR-4, 2 Oz copper board.

## 2 Electrical characteristics

$T_{CASE} = 25\text{ °C}$  unless otherwise specified

**Table 3. On-/off-states**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$V_{GS} = 0\text{ V}$ , $I_D = 250\text{ }\mu\text{A}$	60			V
$I_{DSS}$	Zero gate voltage drain current	$V_{GS} = 0\text{ V}$ , $V_{DS} = 60\text{ V}$			1	$\mu\text{A}$
		$V_{GS} = 0\text{ V}$ , $V_{DS} = 60\text{ V}$ , $T_C = 175\text{ °C}^{(1)}$			10	$\mu\text{A}$
$I_{GSS}$	Gate body leakage current	$V_{DS} = 0\text{ V}$ , $V_{GS} = \pm 20\text{ V}$			$\pm 100$	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$ , $I_D = 250\text{ }\mu\text{A}$	2		4	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}$ , $I_D = 30\text{ A}$		0.014	0.016	$\Omega$

1. Defined by design, not subject to production test.

**Table 4. Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$C_{iss}$	Input capacitance	$V_{DS} = 25\text{ V}$ , $f = 1\text{ MHz}$ , $V_{GS} = 0\text{ V}$	-	1810		pF
$C_{oss}$	Output capacitance		-	360		pF
$C_{riss}$	Reverse transfer capacitance		-	125		pF
$Q_g$	Total gate charge	$V_{DD} = 48\text{ V}$ , $I_D = 60\text{ A}$	-	49	66	nC
$Q_{gs}$	Gate-source charge	$V_{GS} = 0\text{ to }10\text{ V}$	-	18		nC
$Q_{gd}$	Gate-drain charge	(see Figure 12. Test circuit for gate charge behavior)	-	14		nC

**Table 5. Switching times**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 30\text{ V}$ , $I_D = 30\text{ A}$ , $R_G = 4.7\text{ }\Omega$ , $V_{GS} = 10\text{ V}$ (see Figure 11. Test circuit for resistive load switching times and Figure 16. Switching time waveform)	-	16	-	ns
$t_r$	Rise time		-	108	-	ns
$t_{d(off)}$	Turn-off delay time		-	43	-	ns
$t_f$	Fall time		-	20	-	ns

**Table 6. Source-drain diode**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{SD}^{(1)}$	Forward on voltage	$I_{SD} = 60\text{ A}$ , $V_{GS} = 0\text{ V}$	-		1.3	V

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{rr}$	Reverse recovery time	$I_{SD} = 60 \text{ A}$ , $di/dt = 100 \text{ A}/\mu\text{s}$ ,	-	73		ns
$Q_{rr}$	Reverse recovery charge	$V_{DD} = 25 \text{ V}$ , $T_J = 150 \text{ }^\circ\text{C}$	-	182		nC
$I_{RRM}$	Reverse recovery current	(see <a href="#">Figure 13. Test circuit for inductive load switching and diode recovery times</a> )	-	5		A

1. Pulsed: pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5%

## 2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

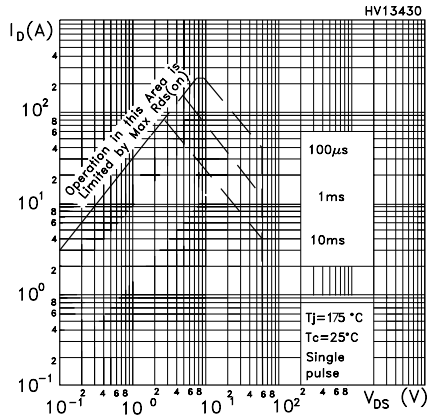


Figure 2. Thermal impedance

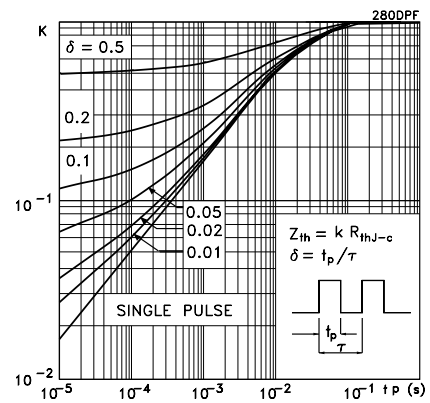


Figure 3. Output characteristics

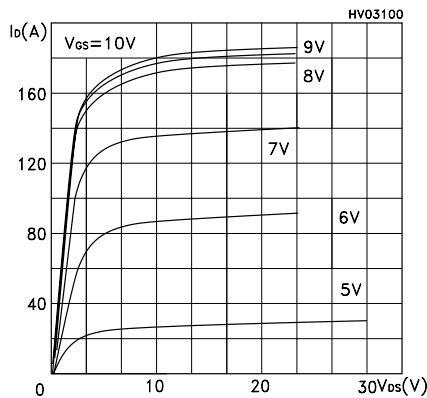


Figure 4. Transfer characteristics

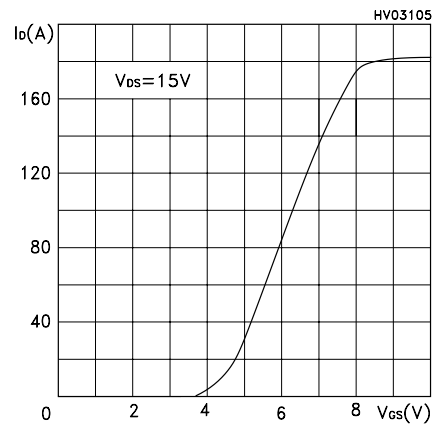


Figure 5. Static drain-source on-resistance

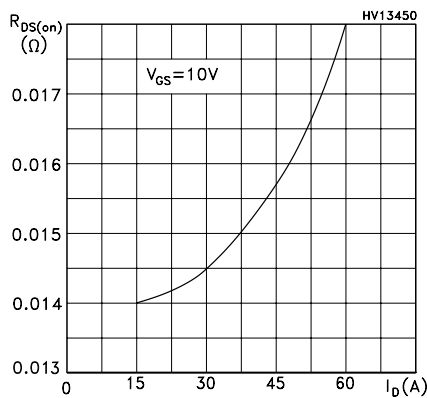
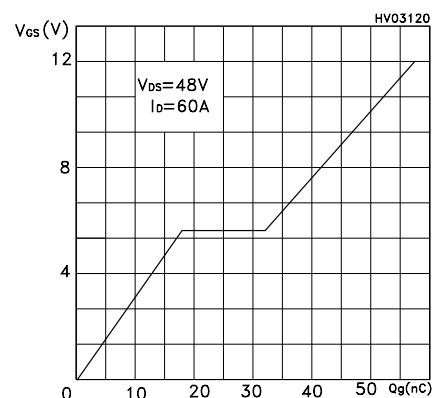
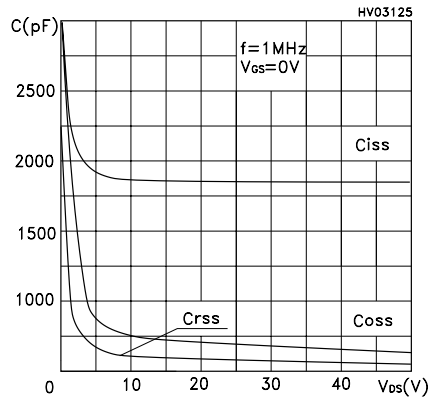


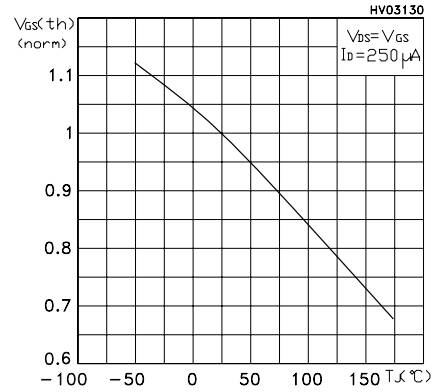
Figure 6. Gate charge vs gate-source voltage



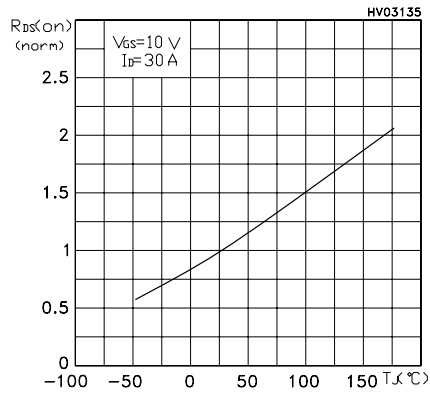
**Figure 7. Capacitance variations**



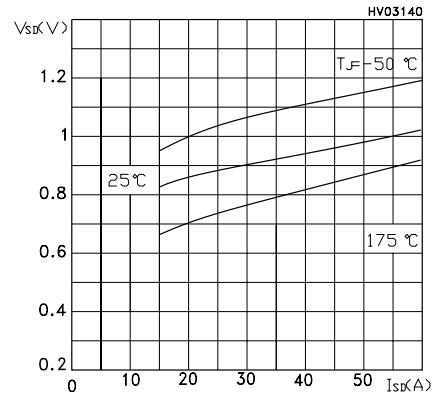
**Figure 8. Normalized gate threshold voltage vs temperature**



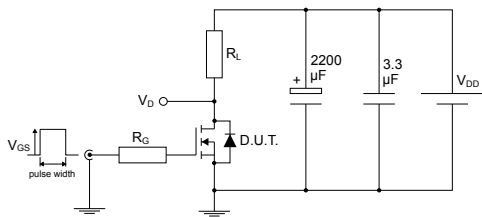
**Figure 9. Normalized on-resistance vs temperature**



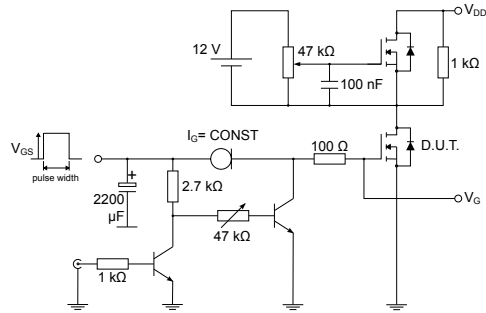
**Figure 10. Source-drain diode forward characteristics**



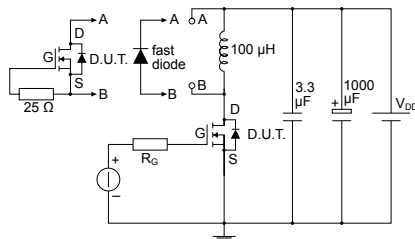
### 3 Test circuits

**Figure 11. Test circuit for resistive load switching times**


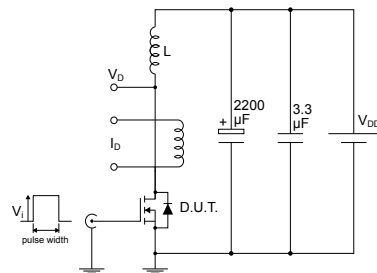
AM01468v1

**Figure 12. Test circuit for gate charge behavior**


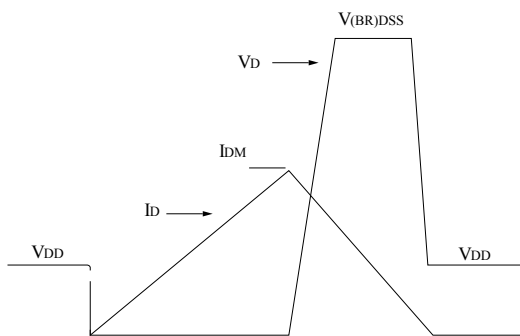
AM01469v1

**Figure 13. Test circuit for inductive load switching and diode recovery times**


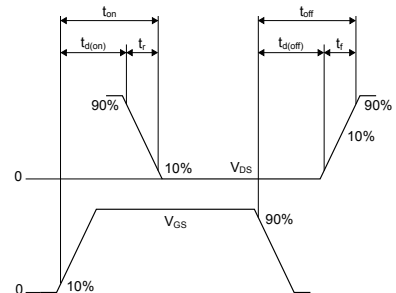
AM01470v1

**Figure 14. Unclamped inductive load test circuit**


AM01471v1

**Figure 15. Unclamped inductive waveform**


AM01472v1

**Figure 16. Switching time waveform**


AM01473v1

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## 4 Package information

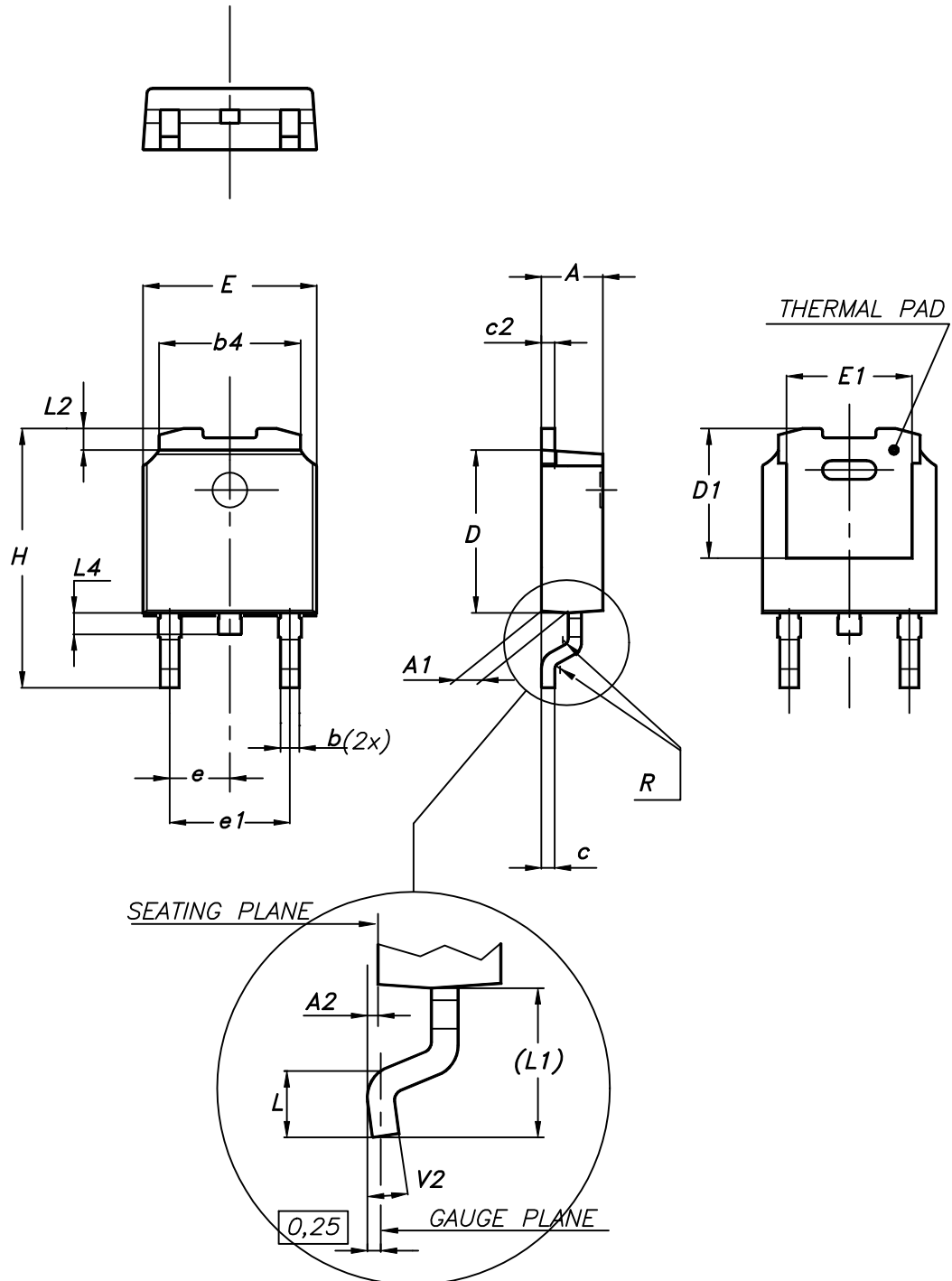
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### 4.1 DPAK (TO-252) type A2 package information

Figure 17. DPAK (TO-252) type A2 package outline



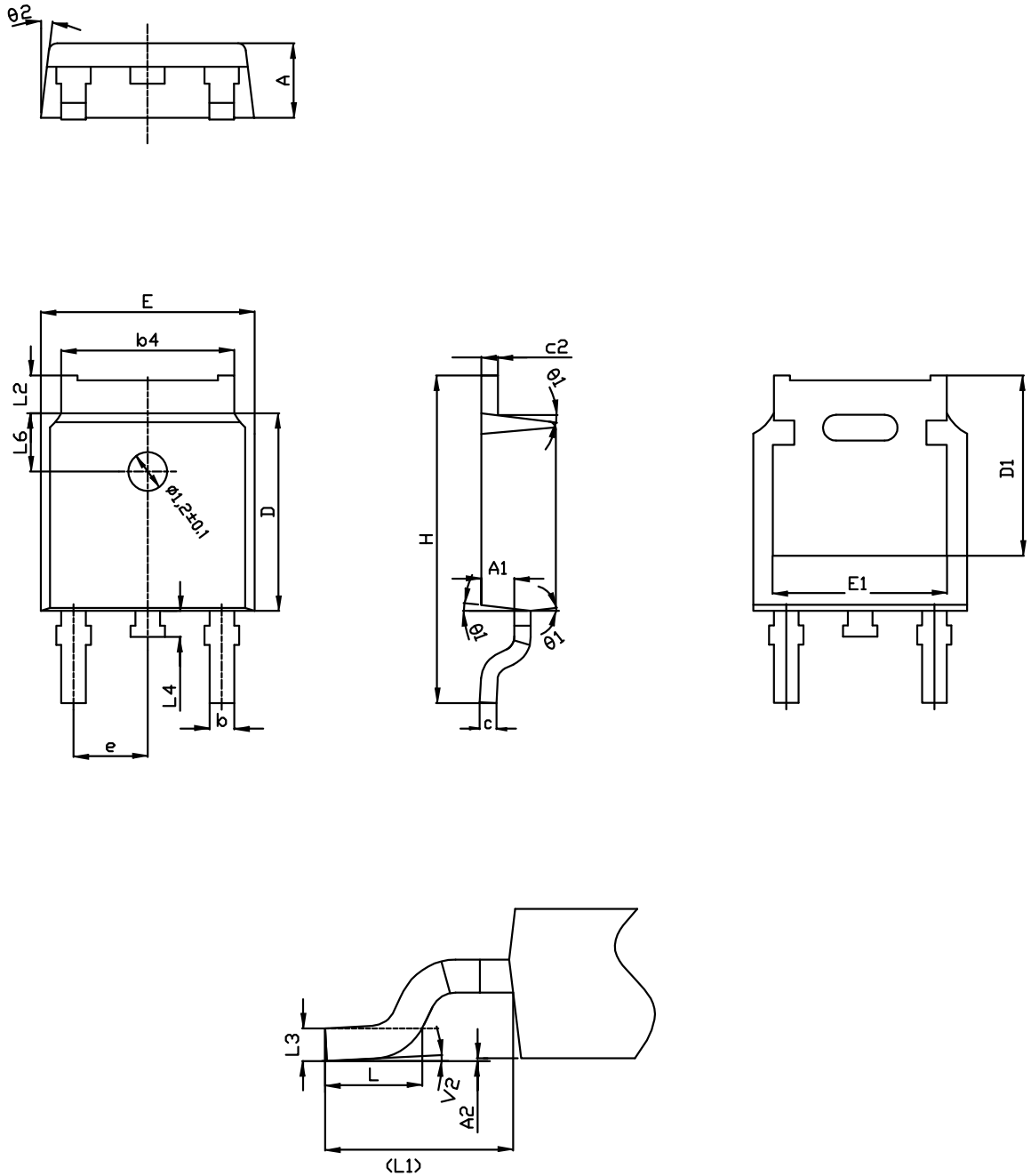
0068772\_type-A2\_rev25

**Table 7. DPAK (TO-252) type A2 mechanical data**

Dim.	mm		
	Min.	Typ.	Max.
A	2.20		2.40
A1	0.90		1.10
A2	0.03		0.23
b	0.64		0.90
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
D1	4.95	5.10	5.25
E	6.40		6.60
E1	5.10	5.20	5.30
e	2.159	2.286	2.413
e1	4.445	4.572	4.699
H	9.35		10.10
L	1.00		1.50
L1	2.60	2.80	3.00
L2	0.65	0.80	0.95
L4	0.60		1.00
R		0.20	
V2	0°		8°

## 4.2 DPAK (TO-252) type C2 package information

Figure 18. DPAK (TO-252) type C2 package outline



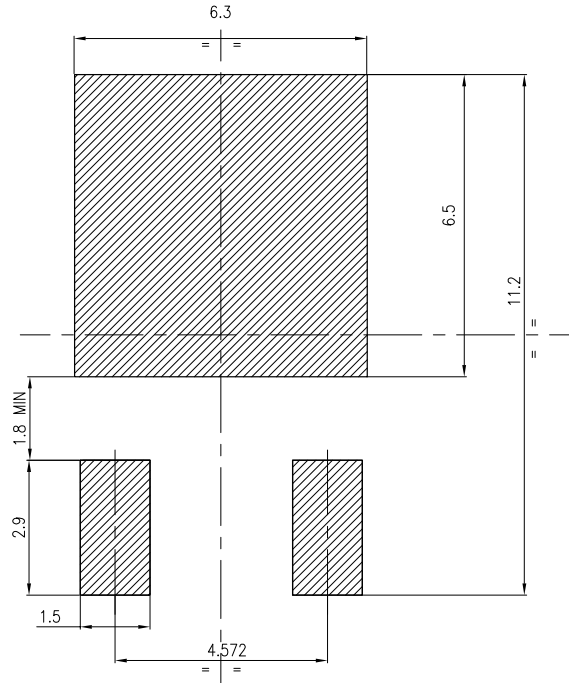
0068772\_C2\_25

**Table 8. DPAK (TO-252) type C2 mechanical data**

Dim.	mm		
	Min.	Typ.	Max.
A	2.20	2.30	2.38
A1	0.90	1.01	1.10
A2	0.00		0.10
b	0.72		0.85
b4	5.13	5.33	5.46
c	0.47		0.60
c2	0.47		0.60
D	6.00	6.10	6.20
D1	5.10		5.60
E	6.50	6.60	6.70
E1	5.20		5.50
e	2.186	2.286	2.386
H	9.80	10.10	10.40
L	1.40	1.50	1.70
L1	2.90 REF		
L2	0.90		1.25
L3	0.51 BSC		
L4	0.60	0.80	1.00
L6	1.80 BSC		
θ1	5°	7°	9°
θ2	5°	7°	9°
V2	0°		8°

### 4.3 DPAK (TO-252) footprint information

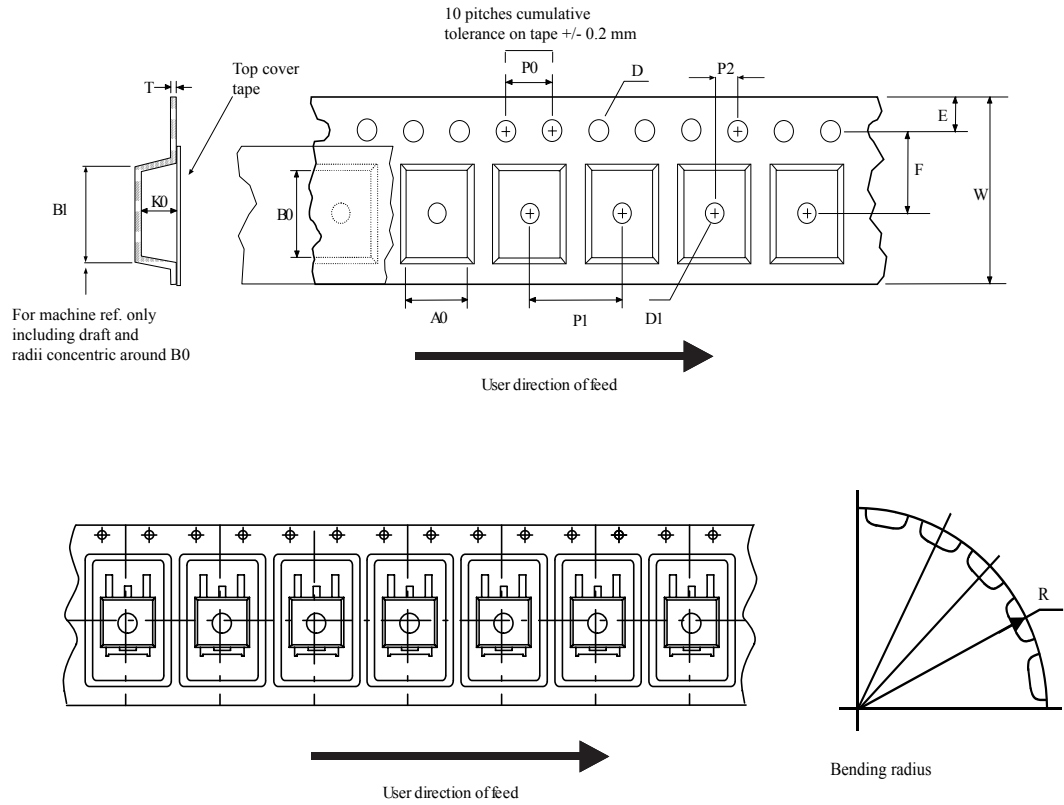
Figure 19. DPAK (TO-252) recommended footprint (dimensions are in mm)



FP\_0068772\_25

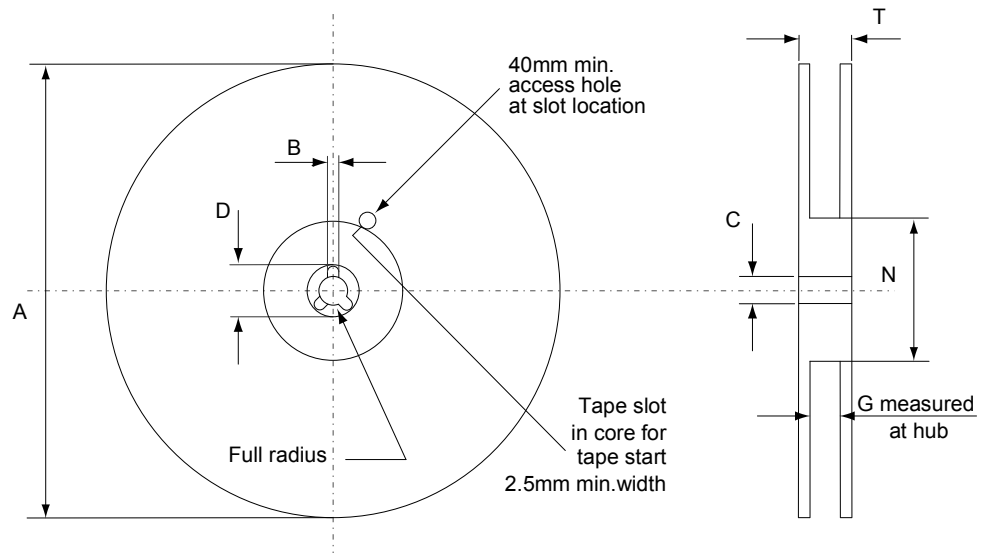
#### 4.4 DPAK (TO-252) packing information

Figure 20. DPAK (TO-252) tape outline



AM08852v1

**Figure 21. DPAK (TO-252) reel outline**



AM06038v1

**Table 9. DPAK (TO-252) tape and reel mechanical data**

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	6.8	7	A		330
B0	10.4	10.6	B	1.5	
B1		12.1	C	12.8	13.2
D	1.5	1.6	D	20.2	
D1	1.5		G	16.4	18.4
E	1.65	1.85	N	50	
F	7.4	7.6	T		22.4
K0	2.55	2.75			
P0	3.9	4.1	Base qty.		2500
P1	7.9	8.1	Bulk qty.		2500
P2	1.9	2.1			
R	40				
T	0.25	0.35			
W	15.7	16.3			

## Revision history

**Table 10. Document revision history**

Date	Version	Changes
03-May-2018	1	Initial release.



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